TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA8069F

4CH LOW SIDE DRIVER

TA8069F is built into four 0.5A low-side driver ICs which drive lamp, relay, and solenoid actuators. Inputs from DI1, DI2, DI3, and DI4 switch ON and OFF modes. Inputs are TTL-compatible, thus the device can also be directly controlled from a CPU or other control system. The device is equipped with low-standby (with all outputs off), self-diagnosis, and protection functions.

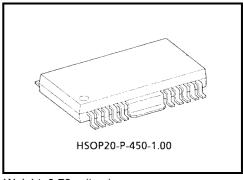
FEATURES

- 0.5A low-side driver
- Four built-in circuits (power supply, self-diagnosis, and protection functions for each circuit)
- Low standby current 0.1mA (Max.)
- Self-diagnosis output

Short : 1A (Typ.)

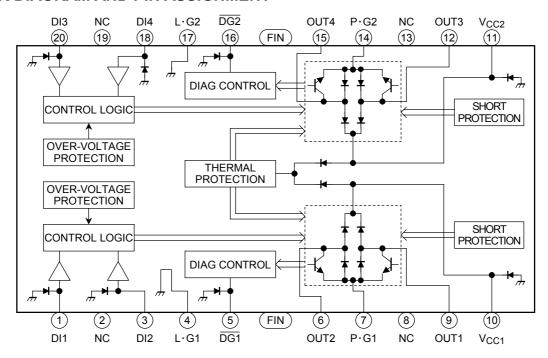
 \overline{DG} 1 : OR output of OUT1 & OUT2 \overline{DG} 2 : OR output of OUT3 & OUT4

- Recommended operating supply voltage range: VCC = 8 V to 16 V
- Multiple protection functions
 Short, thermal, and overvoltage protection functions
- ullet Built-in diodes for absorbing counter electromotive force
- HSOP-20pin power flat package



Weight: 0.79 g (typ.)

BLOCK DIAGRAM AND PIN ASSIGNMENT



PIN DESCRIPTION

PIN No.	SYMBOL	DESCRIPTION
1, 20 3, 18	DI1, DI3 DI2, DI4	Input pins used to control output. H : output on (See Table 1, Truth Table.)
4, 17	L G1, L G2	Ground pins for Logic portion.
5, 16	DG1, DG2	Self-diagnosis output pins (See Table 2, Truth Table & Timing Chart.)NPN transistor open-collector output. When output becomes overcurrent, set to on; duty 97% on (low). At normal operation, set to open (high). DG1: OR output of OUT1 & OUT2 DG2: OR output of OUT3 & OUT4
6, 15 9, 12	OUT2, OUT4 OUT1, OUT3	Connected to load, with sink 0.5A. Features overcurrent detection function to protect IC from instantaneous destruction at load short (See section on Multiple Protections below.) Features diodes for absorbing counter electromotive force built into both V_{CC} and GND sides.
7, 14	P G1, P G2	Ground pins for output portion.
10, 11	V _{CC1} , V _{CC2}	Power supply pins. When more than 30V is applied, overvoltage protection function turns off output to protect the IC and motor load.
2, 8, 13, 19	NC	Not connected. (Electrically, this pin is completely open.)

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TRUTH TABLE 1:1/0

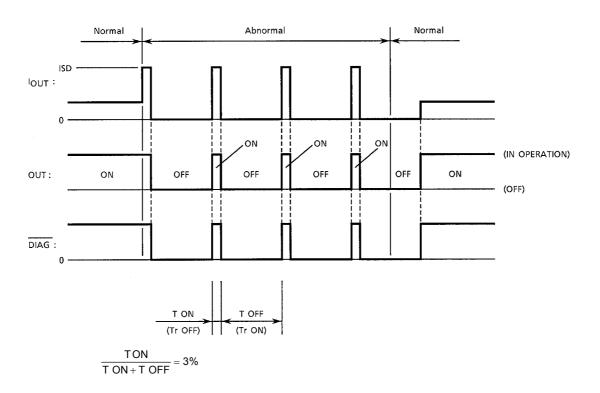
INPUT	OUTPUT	ODEDATING MODE
DI1/2/3/4	OUT1/2/3/4	OPERATING MODE
Н	ON	
L	OFF	
ALL L	OFF (High impedance)	standby

TRUTH TABLE 2: SELF DIAGNOSIS

OUT	OUTPUT		<u> </u>	
OUT1 / 3	OUT2 / 4	LOAD	DIAG	
ON	OFF	Normal	Н	
ON	011	Short	L*	
OFF	ON	Normal	Н	
Oll	ON	Normal Short Normal Short F — Normal	L*	
OFF	OFF	_	Н	
ON	ON	Normal	Н	
ON	ON	Short	L*	

*: TIMING CHART

SELF DIAGNOSIS TIMIGN CHART

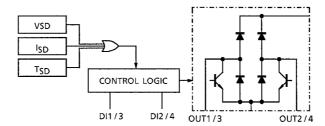


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Multiple protection operation

TA8069F features built-in overvoltage (V_{SD}), overcurrent (I_{SD}), and thermal (T_{SD}) protection functions. These functions protect TA8069F (sometimes motors, too) from deterioration or destruction due to overpower stress. The functions are independent from each other.

Functions are described below.



1. Overvoltage protection (V_{SD})

• Outline

When the voltage supplied to the V_{CC} pin is less than the V_{SD} detection voltage, output is controlled by input signals. When the V_{CC} voltage is greater than the V_{SD} detection voltage, output becomes high impedance (off) regardless of input signals.

Operation

The V_{SD} voltage is detected by comparing the zener voltage with the voltage obtained by dividing V_{CC} by the resistance. If the center voltage of the resistance is higher than the zener voltage, a transistor-off instruction is issued to the control logic portion; if lower, the logic portion is controlled by input signals.

2. Thermal protection (T_{SD})

Outline

When the junction temperature (chip temperature) is less than the TSD detection temperature, output is controlled by input signals. When the junction temperature is greater than the detection temperature, output becomes high impedance regardless of input signals.

Operation

The temperature is detected by monitoring V_F of diodes on the chip. If the diode V_F is lower than the internal reference voltage, a transistor-off instruction is issued to the logic portion; if higher, the logic portion is controlled by input signals.

3. Overcurrent protection (ISD)

Outline

When the output current is less than the ISD detection current, output is controlled by input signals. When the output current is greater than the detection current, output changes to switching waveform as in Figure 1.

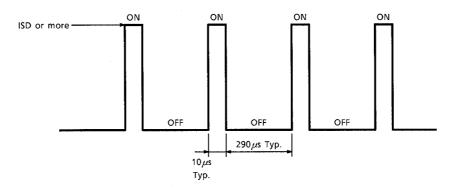


Figure 1 Switching Waveforms

Operation

The output current is detected by monitoring the sense resistance. Detection circuits are connected to the self-diagnosis output pins ($\overline{DG1}$ and $\overline{DG2}$), then further connected to the short circuit protection circuits. When current exceeding the ISD detection current flows to one of the two channels of self-diagnosis output, the corresponding short circuit protection circuit is activated. The short circuit protection circuit is built into the timer. If overcurrent mode continues $10\,\mu$ s (Typ.), the circuit changes the output to high impedance mode, then returns to on mode after $290\,\mu$ s (Typ.). The above switching waveform is output repeatedly as long as the circuit is in overcurrent mode.

· Caution for application

The overcurrent protection is used to protect the IC from instantaneous destruction due to short circuits. If overcurrent continues, configure a system which changes the IC to standby mode using the self diagnosis signal.

Note that the time required for switching the IC from output short (overcurrent detection) to standby must be 1s or less.

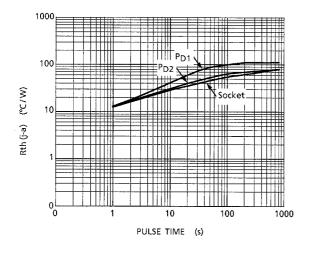
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Power Supply Voltage	V _{CC}	30	٧	
Tower Supply Voltage	V _{CC}	60 (1s)		
Input Voltage	V _{IN}	-0.3V~V _{CC} +0.3	V	
Output Current	I _{O AVE}	0.5	Α	
Operating Temperature	T _{opr}	-40~110	°C	
Storage Temperature	T _{stg}	-55~150	°C	
Lead Temperature time	T _{sol}	260 (10s)	°C	

HSOP20- P-450 THERMAL RESISTANCE DATA (Ta = 25°C)

CHARACTERISTIC	RATING	UNIT	TEST CONDITION
Rθj-a	125	°C/W	_
Rθj-c	13	°C/W	_
P _{D1}	1.0	W	Without radiation board
P _{D2}	1.5	W	60×30×1.6mm 50% Cu mounted
P _{D3}	3.2	W	50×50×1.0mm Iron board mounted
P _{D4}	9.6	W	Infinite radiation board mounted

HSOP20- P-450-1.00 TRANSIENT THERMAL RESISTANCE DATA

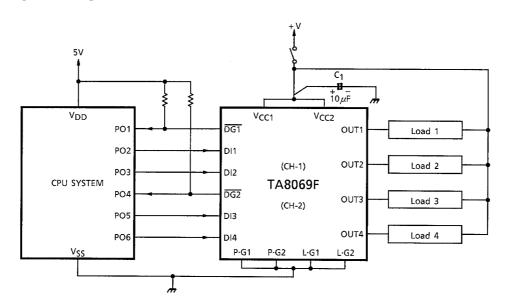


ELECTRICAL CHARACTERISTICS (Unless otherwise specified, V_{CC} = 8~16V, Tc = -40~110°C)

CHARACTERISTIC	SYMBOL	PIN	TEST CIR- CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT	
Power Supply Current	I _{CC1}	V _{CC1} / V _{CC2}	_	Output all off (standby)	_	_	0.1	mA	
Power Supply Current	I _{CC2}	Total	_		_	30	50	IIIA	
logot Valtage	V _{IL}	DI1/2/3/4	_		_	_	0.8	V	
Input Voltage	V _{IH}		_		2.0	_	_		
Input Current	I _{IL}	DI1/2/3/4	_	V _{IN} = 0.4V	_	10	20	μΑ	
	I _{IH}	DI1727374	_	V _{IN} = 5V	_	300	600		
Output Saturation Voltage	V _{SAT}	OUT1/2/3/4	_	I _O = 0.4A	_	1.1	1.3	V	
Output Leakage Current	I _{LEAK-U}	OUT1/2/3/4	_	V _{OUT} = 0V	-10	_	_	μА	
	I _{LEAK-L}		_	V _{OUT} = V _{CC}	_	_	10		
Diada Fannad Valtana	V _{F-U}	OUT1/2/3/4	_	I _F = 0.4A	_	1.5	_	V	
Diode Forward Voltage	V _{F-L}		_		_	1.5	_		
Output Voltage	V _{OL}	DIAG1/2	_	I _{OL} = 3mA	_	_	0.5	V	
Output Leakage Current	I _{LEAK}	DIAG1/2	_	V _{OUT} = V _{CC}	_	_	10	μA	
Overcurrent Detection	I _{SD}		_		_	1.0	_	Α	
Shutdown Temperature	T _{SD}		_		_	150	_	°C	
Overvoltage Detection	V _{SD}		_		_	30	_	V	
Transfer Delay Time	t _P LH		_		_	1	10	μs	
Transfer Delay Time	t _P HL		_		_	1	10	μο	

Note: The parameter values above are guaranteed in the operating voltage rage of 8 V to 16 V. If the guaranteed range is exceeded in practical use, make sure that the IC operates normally in application.

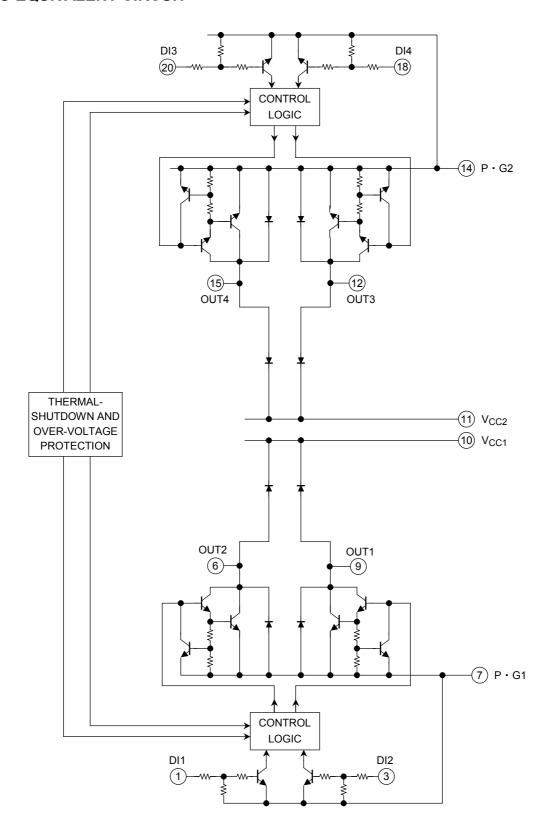
APPLICATION CIRCUIT



*: Cautions for wirings

 C_1 is used for absorbing disturbance or noise. Connect C_1 as near the IC as possible.

I / O EQUIVALENT CIRCUIT



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PACKAGE DIMENSIONS

HSOP20-P-450-1.00

Unit: mm

1.0TYP

16.5MAX

16.0±0.2

16.5MAX

16.0±0.2

1.0TYP

1.0

Weight: 0.79 g (typ.)

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RESTRICTIONS ON PRODUCT USE

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